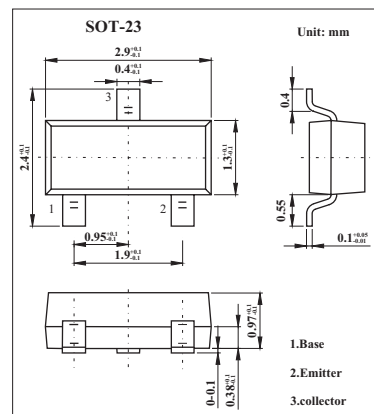


2SA1411

■ Features

- Very high DC current gain:hFE=500 to 1600.
- High V_{EBO} Voltage:V_{EBO}=-10V



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-25	V
Collector-emitter voltage	V _{CEO}	-25	V
Emitter-base voltage	V _{EBO}	-10	V
Collector current	I _C	-150	mA
Total power dissipation at 25°C ambient temperature	P _T	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -25 V, I _E = 0			-100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = -7 V, I _C = 0			-100	nA
DC current gain *	h _{FE}	V _{CE} = -5 V, I _C = -1 mA	500	1000	1600	
Base-emitter voltage *	V _{BE}	V _{CE} = -5 V, I _C = -1 mA		-580		mV
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C = -50mA, I _B = -5mA		-0.15	-0.3	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C = -50mA, I _B = -5mA		-0.8	-1.2	V
Gain bandwidth product	f _T	V _{CE} = -5V, I _E = 10mA		200		MHz
Output capacitance	C _{ob}	V _{CB} = -5V, I _E = 0, f = 1.0MHz		4.6		pF
Turn-on time	t _{on}	V _{CC} = -10V, V _{BE(off)} = 2.7V,		0.12		ns
Storage time	t _{stg}	I _C = -50mA,		0.58		ns
Turn-off time	t _{off}	I _{B1} = -I _{B2} = -1mA		0.75		ns

* PW ≤ 350μs, duty cycle ≤ 2%

■ hFE Classification

Marking	M15	M16
hFE	500~1000	800~1600